ELECTRONIC MATERIALS
MICROELECTRONIC TECHNOLOGIES

UV™135 Positive DUV Photoresist

Advanced Resist for 130 nm Design Rules

Description

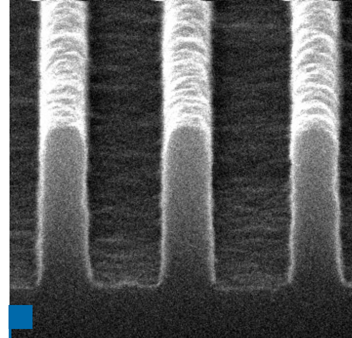
UV135 is an advanced gate resist for use across multiple pitches using a binary mask.

Features Include:

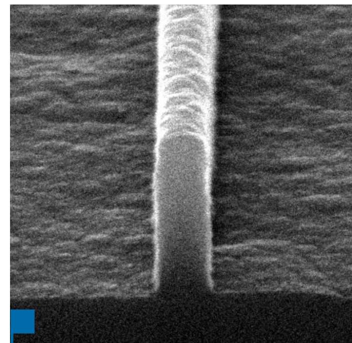
- Low iso-dense bias
- Maximum isolated film retention to <110 nm
- Compatible with PSM and OPC assist features to enlarge process windows

Recommended Process Conditions	
Substrate	200 mm SiON
Thickness	4,900Å
Softbake	120°C/60 sec. Proximity Hotplate
PEB	115°C/60 sec. Proximity Hotplate
Developer	0.26N, 45 sec. single spray puddle

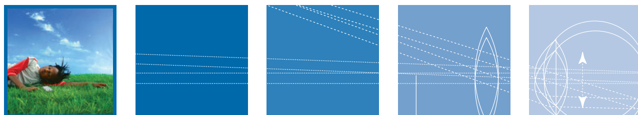
Universal Lithographic Performance



1:1.5 Lines/Spaces at 130 nm



Isolated Lines at 130 nm



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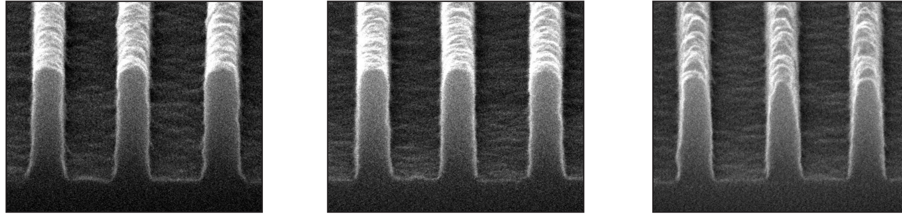
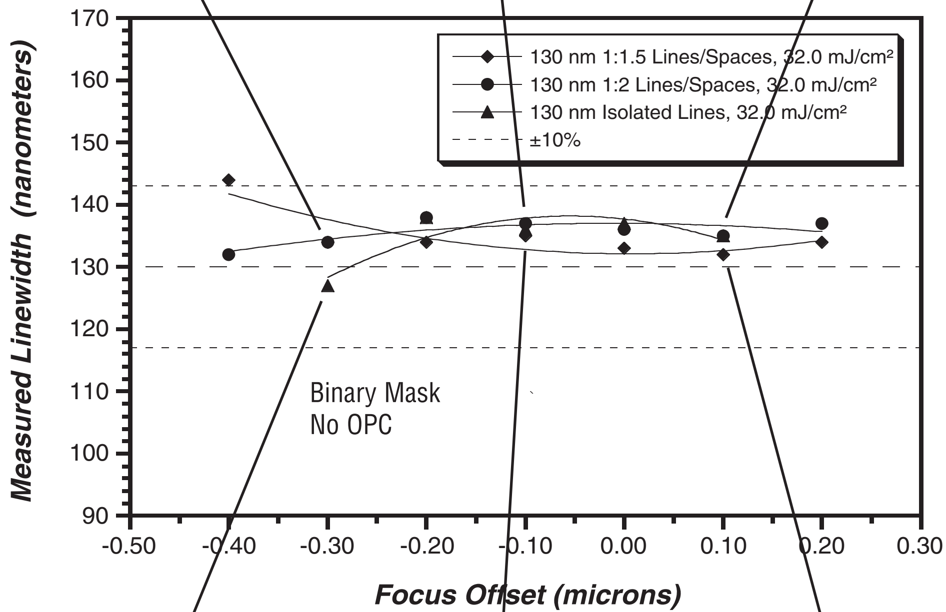
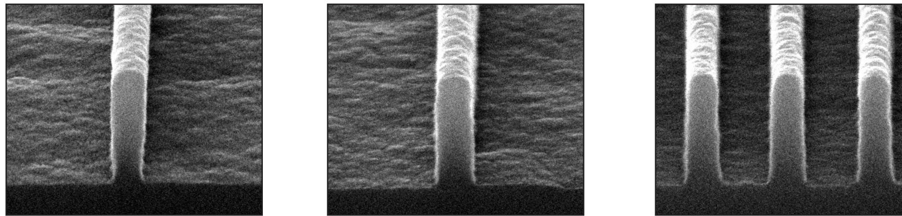
130 nm 1:1.5 Lines/Spaces







130 nm Isolated Lines

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